



**THE DATASHEET OF
SI4838BDY-T1-GE3**





N-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
12	0.0027 at V _{GS} = 4.5 V	34	33 nC
	0.0032 at V _{GS} = 2.5 V	31	
	0.0040 at V _{GS} = 1.8 V	28	

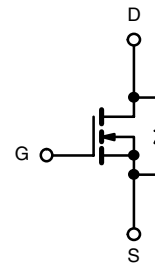
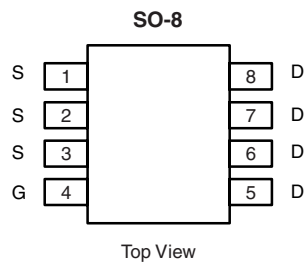
FEATURES

- Halogen-free
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested

RoHS
COMPLIANT

APPLICATIONS

- Low V_{IN} DC/DC



Ordering Information: Si4838BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	12	V
Gate-Source Voltage	V _{GS}	± 8	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	A
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Pulsed Drain Current	I _{DM}	70	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	5.1
		T _A = 25 °C	2.2 ^{b, c}
Single Pulse Avalanche Current	I _{AS}	20	
Avalanche Energy	E _{AS}	20	mJ
Maximum Power Dissipation	P _D	T _C = 25 °C	W
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	39	50	°C/W	
Maximum Junction-to-Foot (Drain)	R _{thJF}	18	22		

Notes:

- Based on T_C = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 85 °C/W.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	12			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		12		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 3.2		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	0.4		1.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 12\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 12\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 4.5\text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}$, $I_D = 15\text{ A}$		0.0021	0.0027	Ω
		$V_{GS} = 2.5\text{ V}$, $I_D = 12\text{ A}$		0.0025	0.0032	
		$V_{GS} = 1.8\text{ V}$, $I_D = 10\text{ A}$		0.0031	0.0040	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 15\text{ A}$		105		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 6\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		5760		pF
Output Capacitance	C_{oss}			1730		
Reverse Transfer Capacitance	C_{rss}			1145		
Total Gate Charge	Q_g	$V_{DS} = 6\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 10\text{ A}$		56	84	nC
				33	50	
Gate-Source Charge	Q_{gs}	$V_{DS} = 6\text{ V}$, $V_{GS} = 2.5\text{ V}$, $I_D = 10\text{ A}$		5.9		
Gate-Drain Charge	Q_{gd}			12.5		
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.2	0.65	1.3	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 6\text{ V}$, $R_L = 0.6\text{ }\Omega$ $I_D \cong 10\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\text{ }\Omega$		25	50	ns
Rise Time	t_r			29	55	
Turn-Off Delay Time	$t_{d(off)}$			140	240	
Fall Time	t_f			35	65	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 6\text{ V}$, $R_L = 0.6\text{ }\Omega$ $I_D \cong 10\text{ A}$, $V_{GEN} = 8\text{ V}$, $R_g = 1\text{ }\Omega$		12	24	
Rise Time	t_r			13	26	
Turn-Off Delay Time	$t_{d(off)}$			56	100	
Fall Time	t_f			10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			5.1	A
Pulse Diode Forward Current ^a	I_{SM}				70	
Body Diode Voltage	V_{SD}	$I_S = 3\text{ A}$		0.60	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$		52	100	ns
Body Diode Reverse Recovery Charge	Q_{rr}			40	80	nC
Reverse Recovery Fall Time	t_a			21		ns
Reverse Recovery Rise Time	t_b			31		

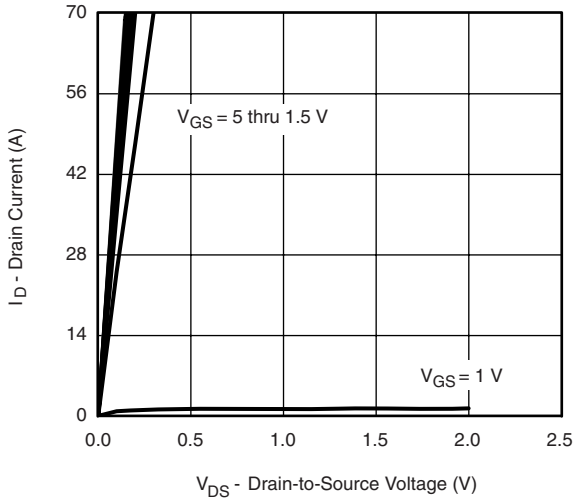
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

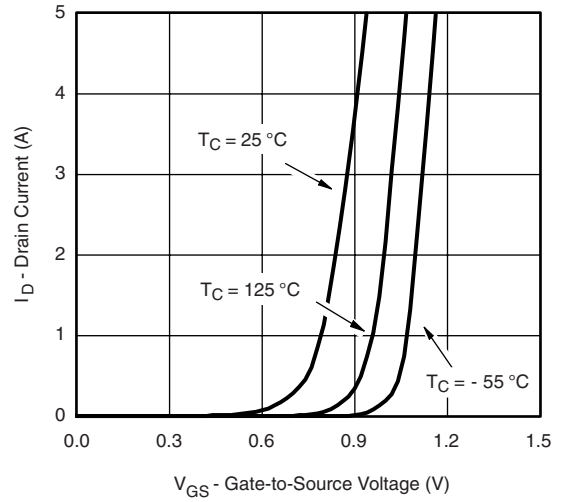
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



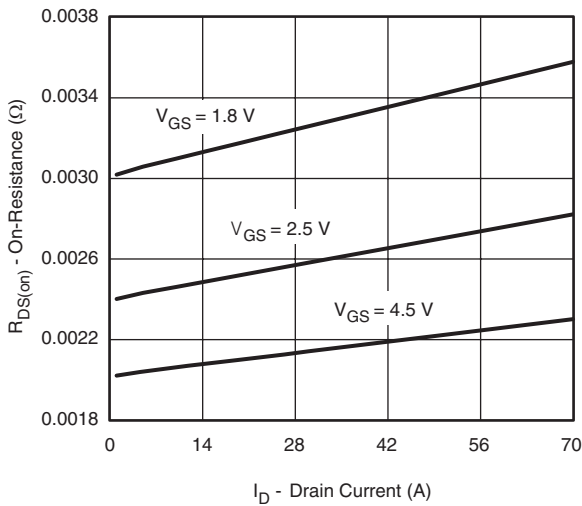
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



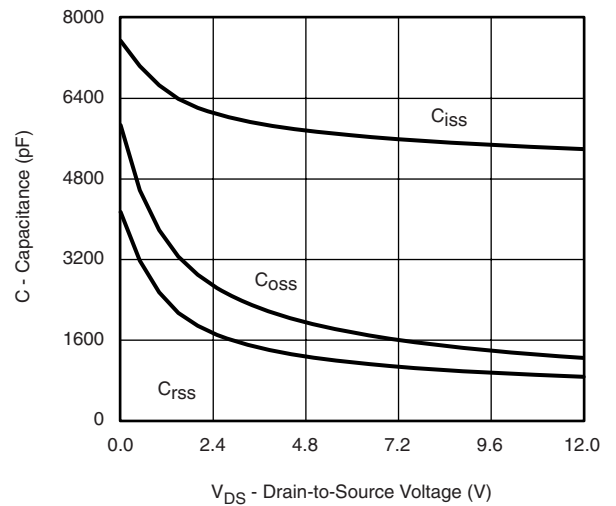
Output Characteristics



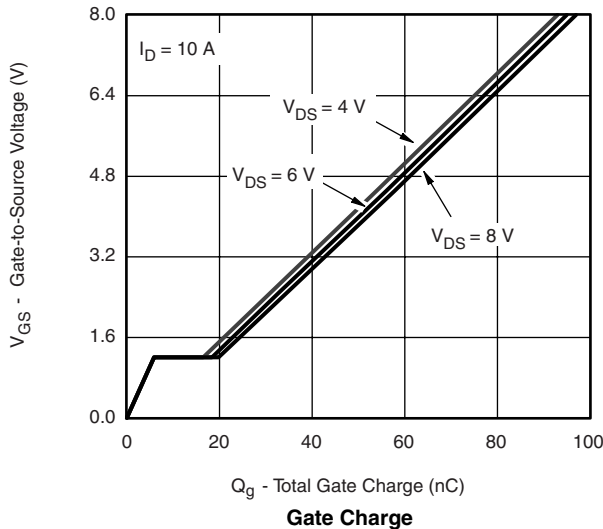
Transfer Characteristics



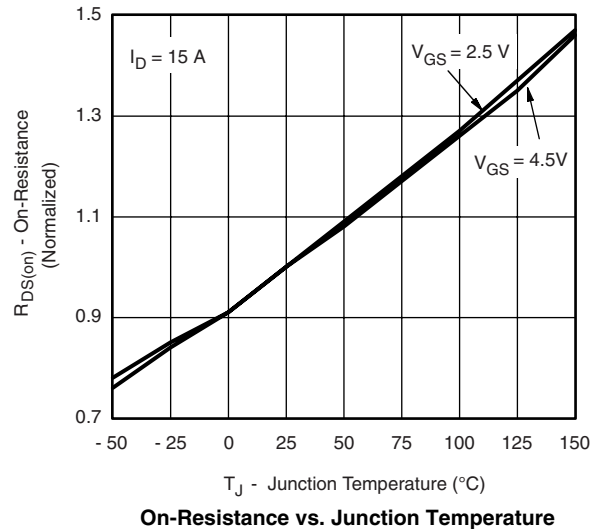
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



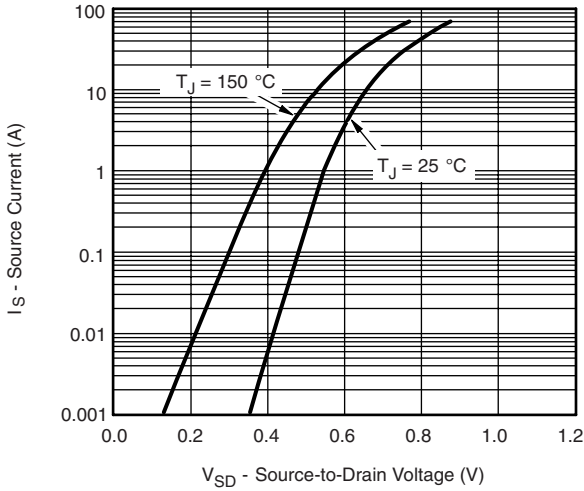
Gate Charge



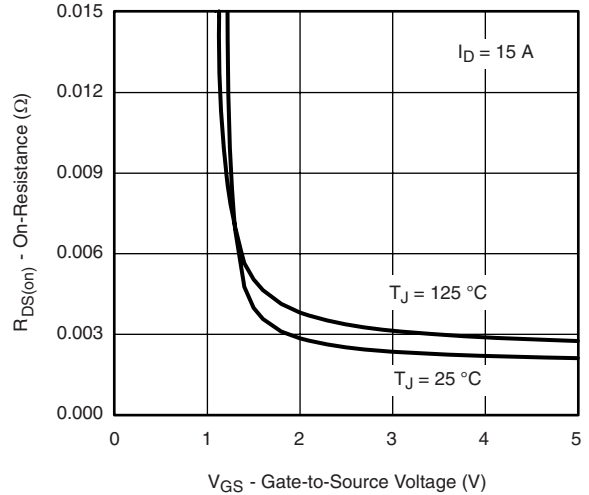
On-Resistance vs. Junction Temperature



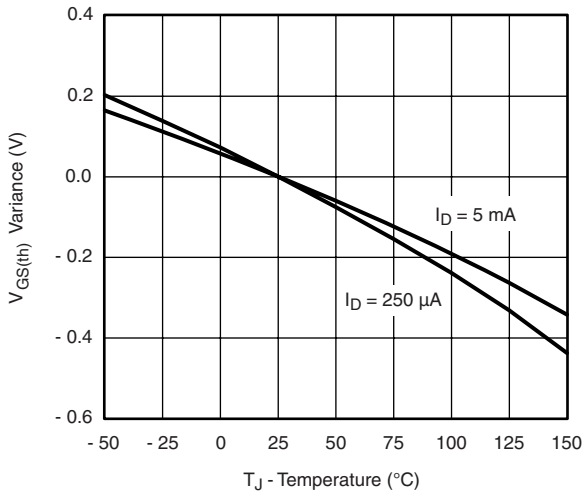
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



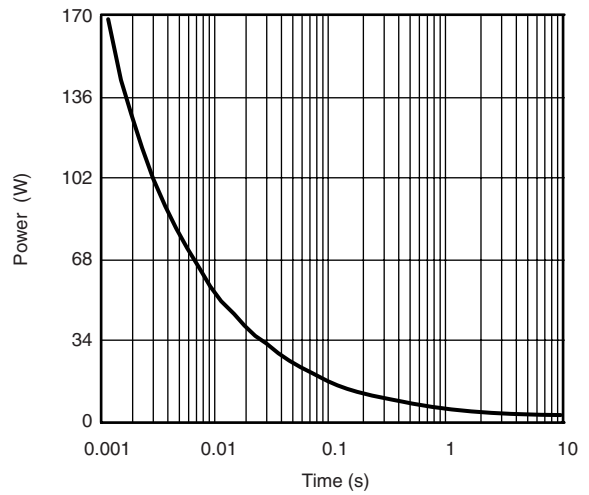
Source-Drain Diode Forward Voltage



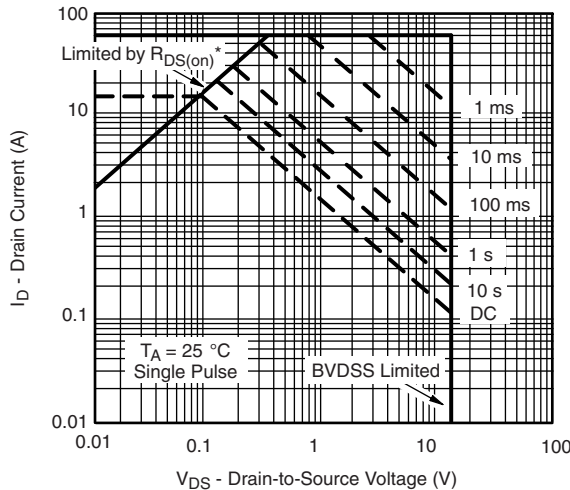
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

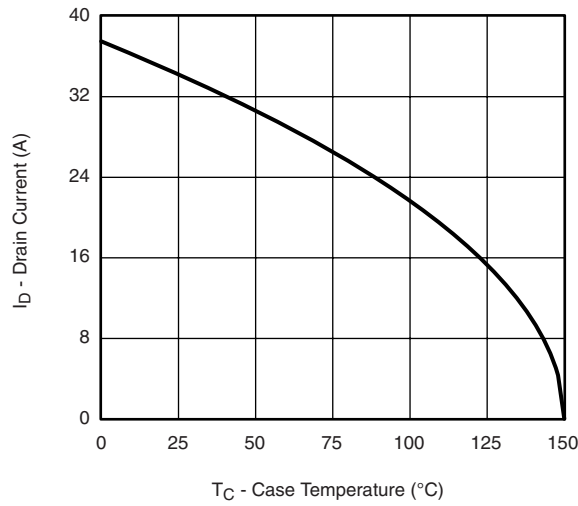


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

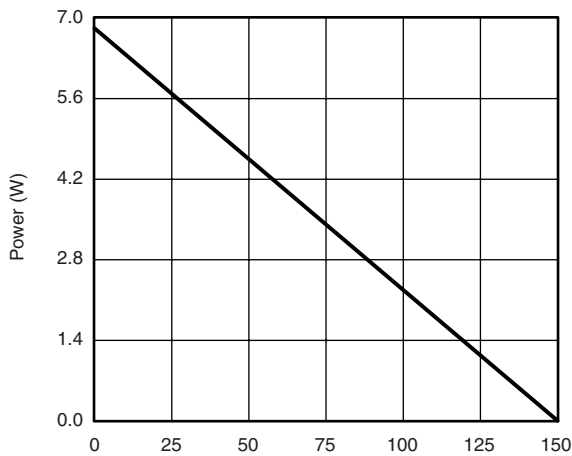
Safe Operating Area, Junction-to-Ambient



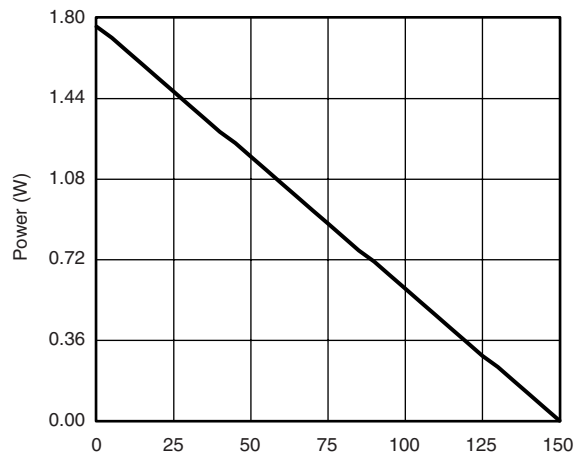
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



Power, Junction-to-Foot

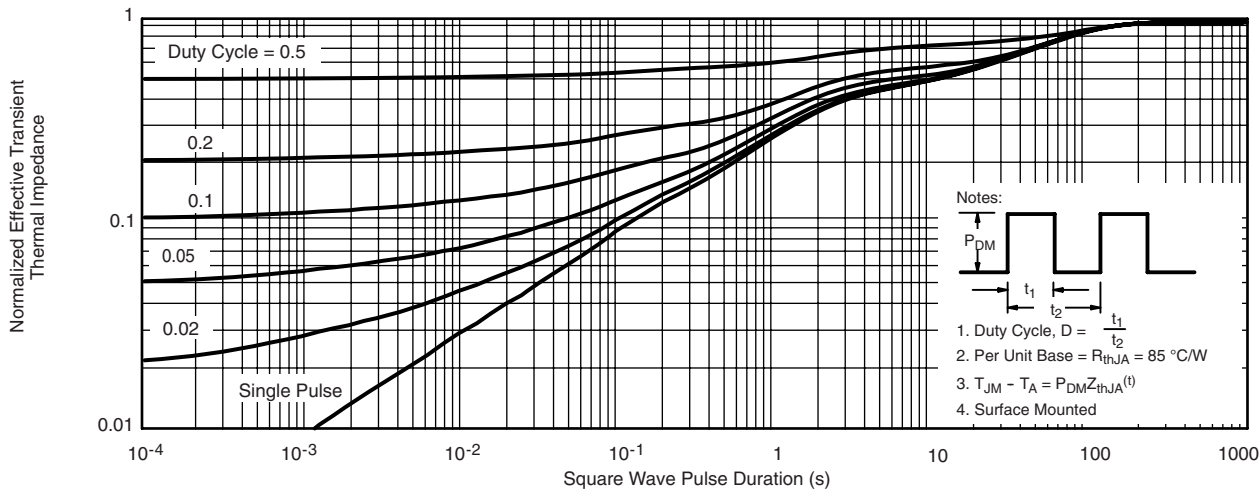


Power, Junction-to-Ambient

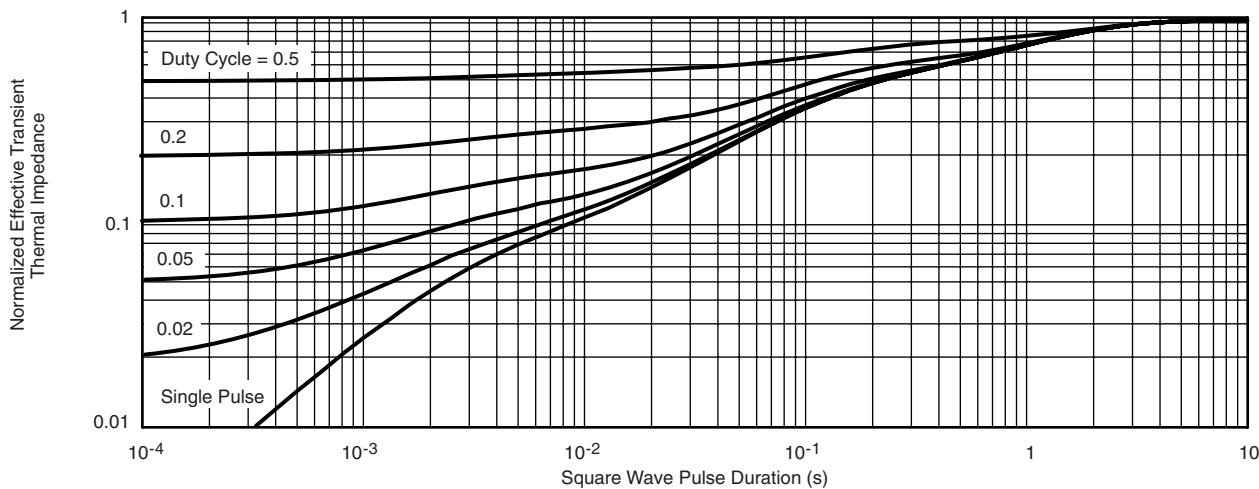
*The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

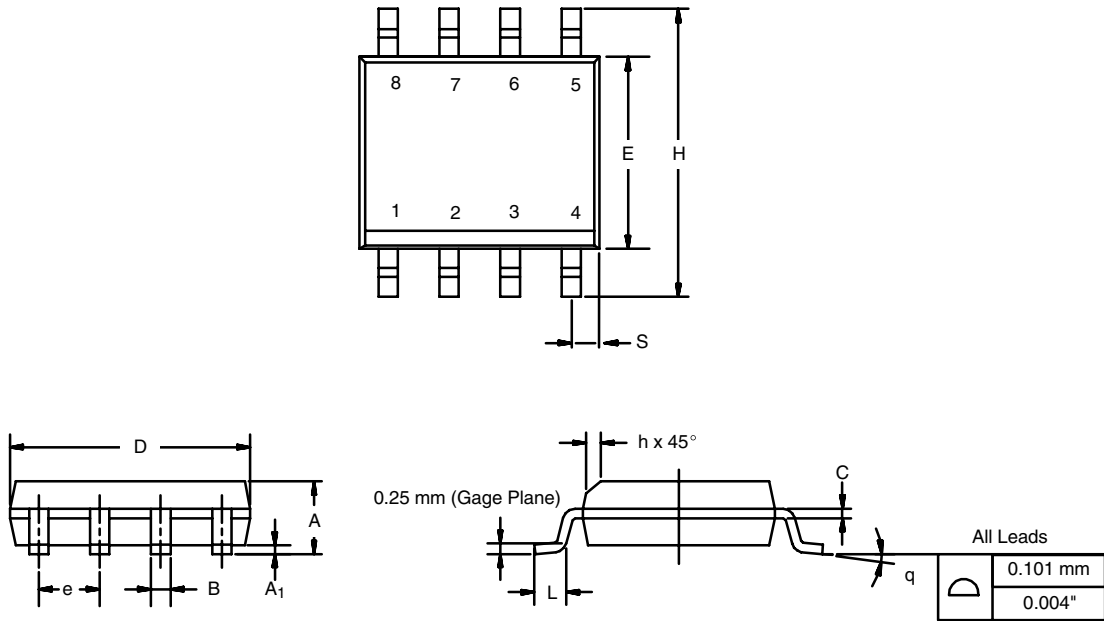


Normalized Thermal Transient Impedance, Junction-to-Foot

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SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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